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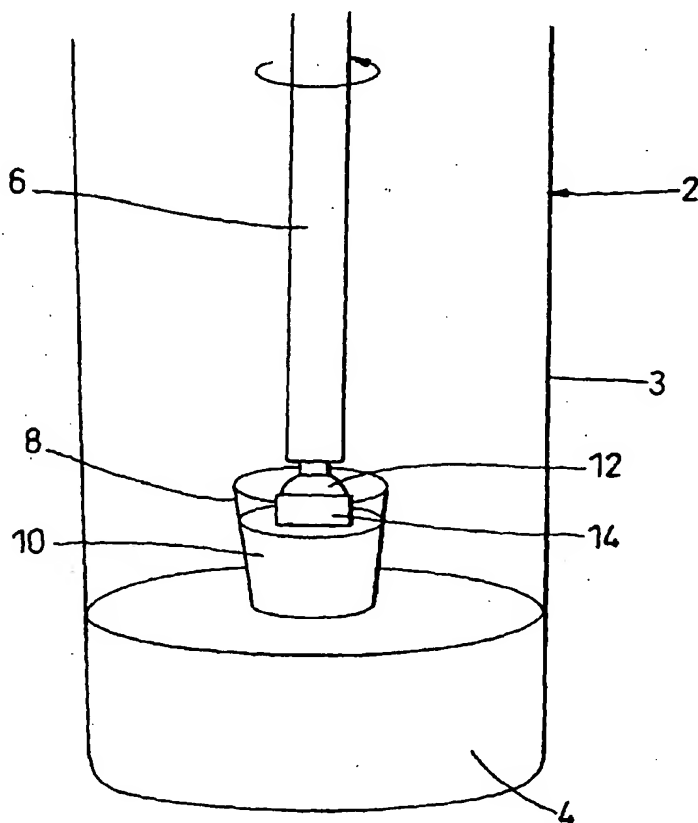
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(54) Title: METHOD OF MANUFACTURING DOPED SUPERCONDUCTING MATERIALS



(57) Abstract: The invention provides a method of manufacturing a doped i X-Ba-Cu-O material, the method comprising the steps of: a) mixing an X-Ba-L-O or X-Ba-Cu-L-O material with an X-1 Ba-Cu-O material; and b) crystallising the mixture; 1 wherein each X is independently selected from a rare earth (Group IIIB) element, yttrium, a combination of rare earth elements, or a combination of yttrium and a rare earth element; and L is selected from U, Nb, Ta, Mo, W, Zr, Hf, Ag, Pt, Ru and Sn. The invention further provides a doped material manufactured by the method of the invention.

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